Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel emitter-collector diode in a SOT54 (TO-92) plastic package.

2. Features and benefits

- · High typical DC current gain
- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode

3. Applications

- Compact fluorescent lamps (CFL)
- · Low power electronic lighting ballasts
- · Off-line self-oscillating power supplies (SOPS) for battery charging

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Val	lues		Unit	
Absolute	Absolute maximum rating							
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		7	00		V	
I _c	collector current	DC	1.5			Α		
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	2.1 V		W			
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
h _{FE}	DC current gain	$I_{C} = 0.5 \text{ A}; V_{CE} = 2 \text{ V}; T_{j} = 25 \text{ °C}$		8	17	25		

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C I
2	С	collector]	
3	E	emitter	3 2 1 TO-92 (SOT54)	B E E sym131

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PHD13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54				

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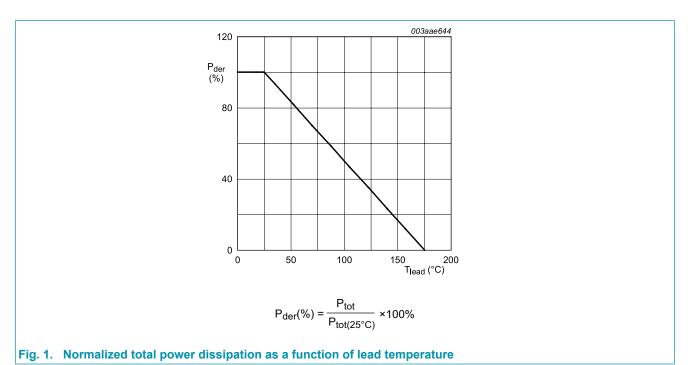
7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	700	V
V _{CBO}	collector-base voltage	I _E = 0 A	700	V
V_{CEO}	collector-emitter voltage	I _B = 0 A	400	V
Ic	collector current	DC	1.5	Α
I _{CM}	peak collector current		3	Α
I _B	base current	DC	0.75	Α
I _{BM}	peak base current		1.5	А
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	2.1	W
T _{stg}	storage temperature		-65 to 150	°C
T _j	junction temperature		150	°C
V_{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	9	V

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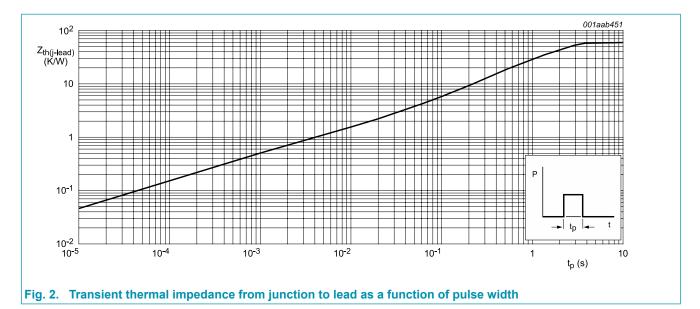


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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	Fig. 2	-	-	60	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W



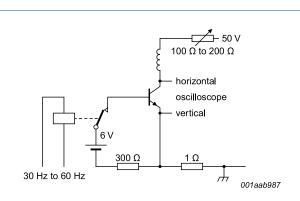
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics		,		,	
	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 700 V	-	-	1	mA
	current	V _{BE} = 0 V; V _{CE} = 700 V; T _j =100°C	-	-	5	mA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{lead} = 25^{\circ}\text{C}$	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25^{\circ}\text{C}$	-	-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25^{\circ}\text{C}; \underline{\text{Fig. 3}}; \underline{\text{Fig. 4}}$	400	-	-	V
V _{CEsat}	collector-emitter	$I_{\rm C} = 0.5 \text{A}; I_{\rm B} = 0.1 \text{A}; T_{\rm lead} = 25 ^{\circ}\text{C}$	-	-	0.5	V
	saturation voltage	I _C = 1 A; I _B = 0.25 A; T _{lead} = 25°C	-	-	1	V
		I _C = 1.5 A; I _B = 0.5 A; T _{lead} = 25°C	-	-	1.5	V
V _{BEsat} base-emitter saturation voltage	base-emitter saturation	I _C = 0.5 A; I _B = 0.1 A; T _{lead} = 25°C	-	-	1	V
	voltage	I _C = 1 A; I _B = 0.25 A; T _{lead} = 25°C	-	-	1.2	V
V _F	forward voltage	I _F = 0.5 A; T _j = 25°C	-	-	1.5	V
h _{FE}	DC current gain	I _C = 0.5 A; V _{CE} = 2 V; T _j = 25°C	8	17	25	
		I _C = 1 A; V _{CE} = 2 V; T _j = 25°C	5	9	15	
Dynamic	characteristics					
t _{on}	turn-on time	I_C = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_L = 75 Ω ; T_{Iead} = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	1	μs
t _s	storage time	I_{C} = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_{L} = 75 Ω ; T_{lead} = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	4	μs
		I_C = 1 A; I_{Bon} = 0.2 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.8	-	μs
t _f	fall time	I_{C} = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_{L} = 75 Ω ; T_{lead} = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	0.7	μs
		I_{C} = 0.5 A; I_{Bon} = 0.1 A; V_{BB} = -5 V; L_{B} = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.1	-	μs

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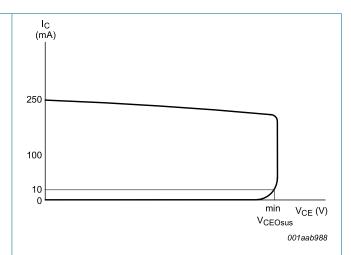
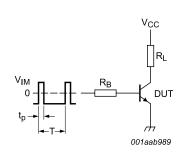


Fig. 3. Test circuit for collector-emitter sustaining voltage

Fig. 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



 V_{IM} = -6 V to + 8 V; V_{CC} = 250 V; t_{p} = 20 μs ; δ = t_{p}/T = 0.01.

 R_{B} and R_{L} calculated from I_{Con} and I_{Bon} requirements

Fig. 5. Test circuit for resistive load switching

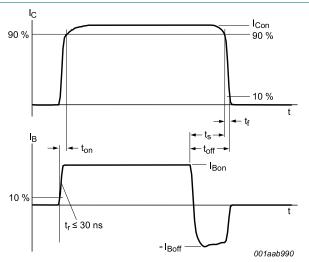
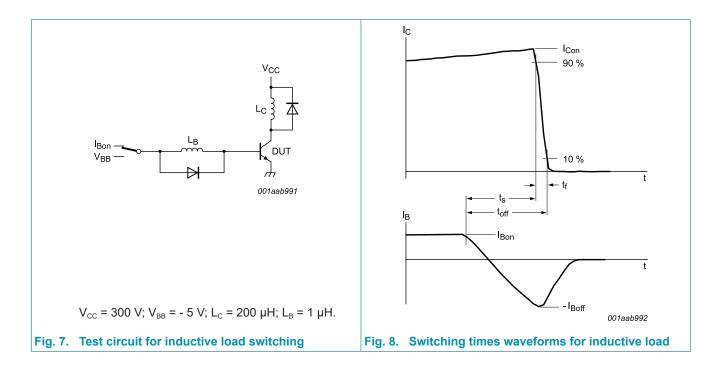


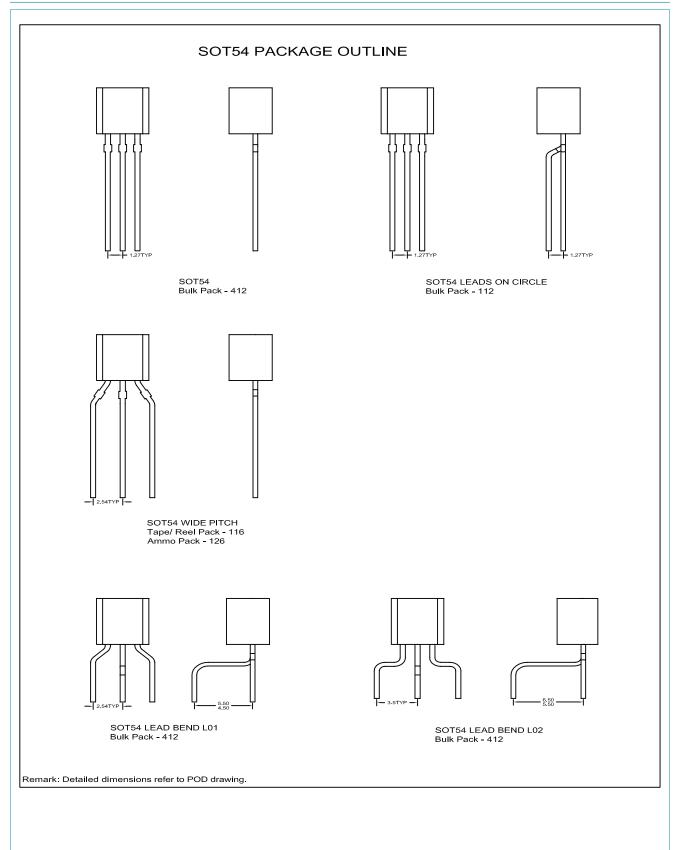
Fig. 6. Switching times waveforms for resistive load

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10. Package outline



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11. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PHD13003C v.2	20180224	Product data sheet	-	PHD13003C v.1		
Modifications:	odifications: Change from NXP version to WeEn version					
PHD13003C v.1	20100729	Product data sheet	-	-		

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 29 May 2018

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